

S10U200FCT

Trench MOS Schottky Rectifier

REVERSE VOLTAGE - 200 Volts FORWARD CURRENT - 10.0 Amperes

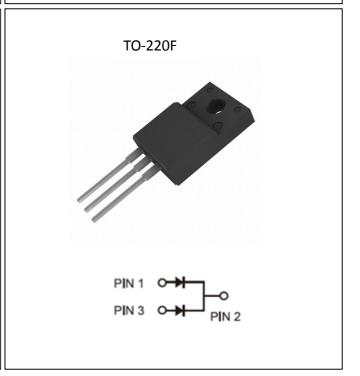
FEATURES

- · Low power loss, high efficiency
- Low forward voltage drop
- High forward surge capability
- High frequency operation
- · Excellent high temperature stability
- Trench MOS Schottky technology

MECHANICAL DATA

Case: TO-220FPolarity: As marked

Weight: Approximated 1.86 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Characteristics	Symbol	Value		Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	200		V
RMS Reverse Voltage	V_{RMS}	140		V
Forward Voltage Drop		Тур.	Max.	
I _F =3A (T _J =25°C)		0.82	-	
I _F =3A (T _J =125°C)	V_{F}	0.6	-	V
I _F =5 A (T _J =25°ℂ)		0.95	1.05	
I _F =5 A (T _J =125°C)		0.65	0.76	
Maximum Reverse Current at Rated V _{RRM}		Тур.	Max.	
T _J =25°C	I_{R}	5	50	μA
T _J =125°C		3	10	mA
Maximum Average Forward Rectified Current				
Total device	Ι _Ο	10		Α
Per diode		5		
Peak Forward Surge Current,				
8.3 ms Single Half Sine-wave	I_{FSM}	80		Α
Superimposed on Rated Load (JEDEC method)				
Peak Repetitive Reverse Current at tp=2 μs, 1 kHz,	I _{RRM}	1.0		Α
Operating and StorageTemperature Range	$T_{J,} T_{STG}$	-65 to +150		°C



Rating and Characteristic Curves

